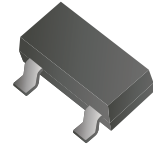


CDSV3-19-G/20-G/21-G High Speed RoHS Device

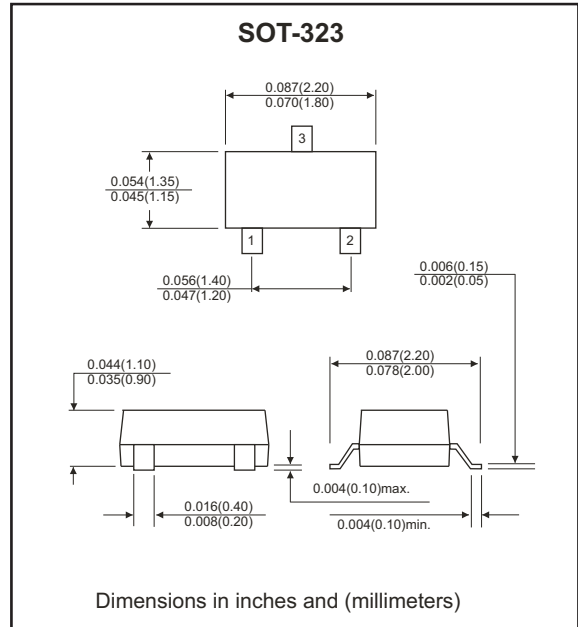
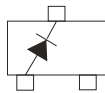


Features

- Fast switching diode.
- Surface mount package ideally for automatic insertion.
- For general purpose switching applications.
- High conductance.

Mechanical data

- Case: SOT-323
- Terminals: Solder plated, solderable per MIL-STD-750, Method 2026.
- Marking: CDSV3-19-G KA8
CDSV3-20-G KT2
CDSV3-21-G KT3



Maximum Rating (at Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Power dissipation	P_D	200	mW
Forward current	I_F	200	mA
Reverse voltage	V_R	CDSV3-19-G: 120 CDSV3-20-G: 150 CDSV3-21-G: 200	V
Junction and storage temperature	T_J, T_{STG}	-55 ~ +150	°C

Electrical Characteristics (at Ta=25°C unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Max	Unit
Reverse breakdown voltage	$V_{(BR)R}$	$I_R=100\mu A$	100 150 200		V
Reverse leakage current	I_R	$V_R=100V$ $V_R=150V$ $V_R=200V$		0.1	UA
Forward voltage	V_F	$I_F=100mA$ $I_F=200mA$		1 1.25	V
Diode capacitance	C_D	$V_R=0V, f=1MHz$		5	pF
Reverse recovery time	t_{rr}	$I_F=I_R=30mA, I_{rr}=0.1 \times I_R$		50	nS

Characteristic Curves (CDSV3-19-G/20-G/21-G)

Fig.1 - Forward Characteristics

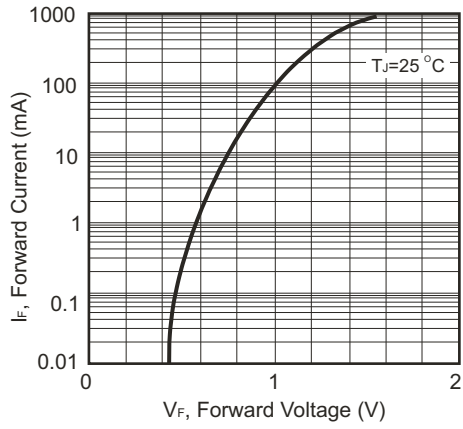


Fig.2 - Leakage Current vs Junction Temperature

